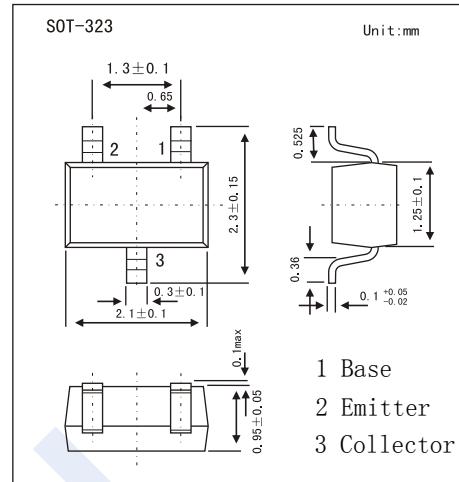


PNP Transistors

2SA1979UF

■ Features

- Large collector current : $I_{CMax} = -500mA$
- Complements to 2SC5342UF



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-40	V
Collector - Emitter Voltage	V_{CEO}	-32	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{Stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = -100 \mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -1 mA, I_B = 0$	-32			
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -10mA$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -1V, I_C = -100mA$	70		240	
Collector output capacitance	C_{ob}	$V_{CB} = -6V, I_E = 0, f = 1MHz$		7.5		pF
Transition frequency	f_T	$V_{CE} = -6V, I_C = -20mA$		200		MHz

■ Classification of h_{FE}

Type	2SA1979UF-O	2SA1979UF-Y
Range	70-140	120-240
Marking	AO	AY

PNP Transistors

2SA1979UF

■ Typical Characteristics

Fig. 1 $P_C - T_a$

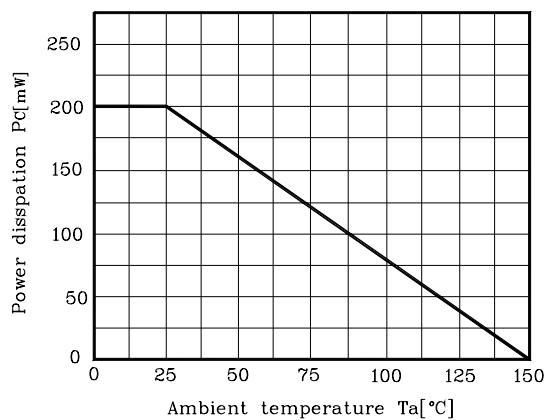


Fig. 3 $I_C - V_{CE}$

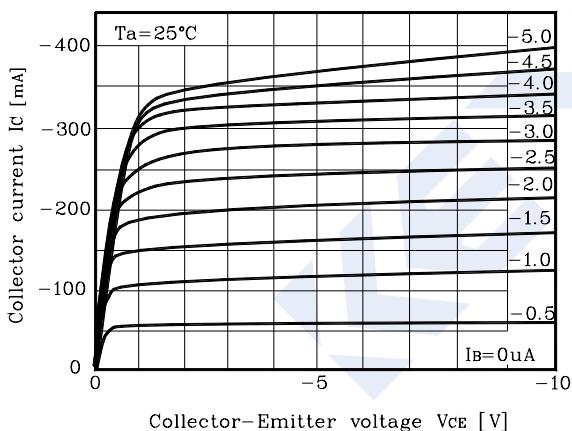


Fig. 5 $h_{FE} - I_C$

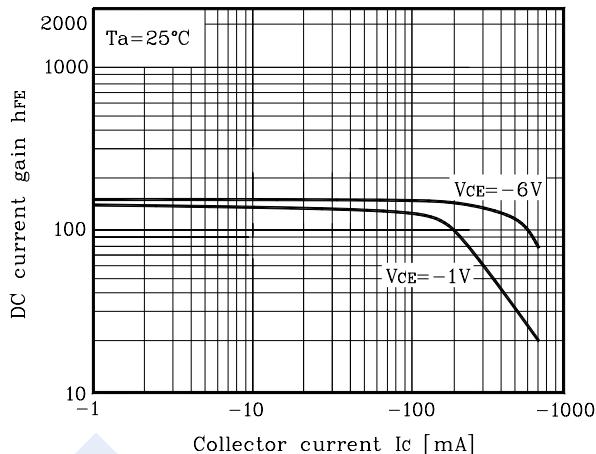


Fig. 2 $I_C - V_{BE}$

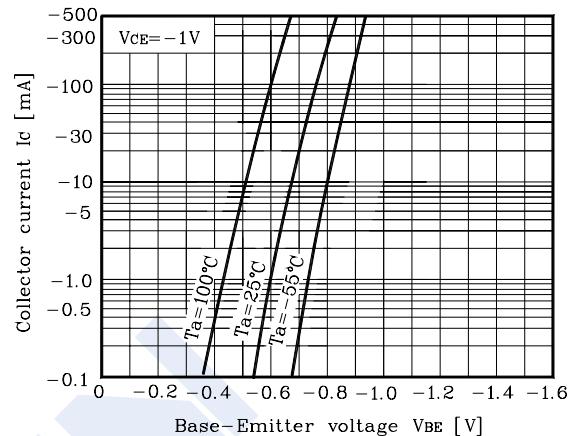


Fig. 4 $V_{CE(sat)} - I_C$

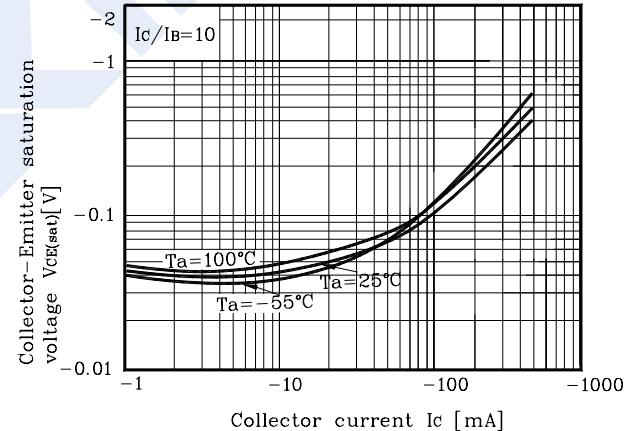


Fig. 6 $h_{FE} - I_C$

